

# LS130A MONOLITHIC DUAL PNP TRANSISTOR



# Linear Systems replaces discontinued Intersil IT130A

The LS130A is a monolithic pair of PNP transistors mounted in a single TO-71 package. The monolithic dual chip design reduces parasitics and gives better performance while ensuring extremely tight matching. The LS130A is a direct replacement for discontinued Intersil IT130A.

The hermetically sealed TO-71 is well suited for hi-rel and harsh environment applications.

(See Packaging Information).

#### LS130A Features:

- High h<sub>fe</sub> at low current
- Tight matching
- Tight V<sub>BE</sub> tracking
- Low Output Capacitance

FEATURES							
Direct Replacement for INTERSIL IT130A							
HIGH h <sub>FE</sub> @ LOW CURRENT	≥ 200 @ 10µA						
OUTPUT CAPACITANCE	≤ 2.0pF						
V <sub>BE</sub> tracking	≤ 3.0μV°C						
ABSOLUTE MAXIMUM RATINGS 1							
@ 25°C (unless otherwise noted)							
Maximum Temperatures							
Storage Temperature	-65°C to +200°C						
Operating Junction Temperature -55°C to +150°							
Maximum Power Dissipation							
Continuous Power Dissipation (One side)	250mW						
Continuous Power Dissipation (Both sides)	500mW						
Linear Derating factor (One side)	2.3mW/°C						
Linear Derating factor (Both sides)	4.3mW/°C						
Maximum Currents							
Collector Current	10mA						

### MATCHING CHARACTERISTICS @ 25°C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
V <sub>BE1</sub> - V <sub>BE2</sub>	Base Emitter Voltage Differential			1	mV	$I_C = 10 \mu A$ , $V_{CE} = 5 V$
$\Delta  (V_{BE1} - V_{BE2})  / \Delta T$	Base Emitter Voltage Differential			3	μV/°C	$I_C = 10 \mu A, V_{CE} = 5 V$
	Change with Temperature					T <sub>A</sub> = -55°C to +125°C
I <sub>B1</sub> - I <sub>B2</sub>	Base Current Differential			2.5	nA	$I_C = 10\mu A$ , $V_{CE} = 5V$

## ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

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SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
BV <sub>CBO</sub>	Collector to Base Voltage	45	-		V	$I_{c} = 10 \mu A, I_{E} = 0$
BV <sub>CEO</sub>	Collector to Emitter Voltage	45	1		٧	$I_{\rm C} = 10 \mu A, I_{\rm B} = 0$
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	6.2			V	$I_E = 10 \mu A$ , $I_C = 0^2$
BV <sub>cco</sub>	Collector to Collector Voltage	60			V	$I_{C} = 10 \mu A, I_{E} = 0$
h <sub>FE</sub>	DC Current Gain	200				$I_{C} = 10 \mu A, V_{CE} = 5 V$
		225				$I_C = 1.0 \text{mA}, V_{CE} = 5 \text{V}$
V <sub>CE</sub> (SAT)	Collector Saturation Voltage			0.5	V	$I_{C} = 0.5 \text{mA}, I_{B} = 0.05 \text{mA}$
I <sub>EBO</sub>	Emitter Cutoff Current			1	nA	$I_{C} = 0, V_{EB} = 3V$
I <sub>CBO</sub>	Collector Cutoff Current			1	nA	$I_E = 0$ , $V_{CB} = 45V$
C <sub>OBO</sub>	Output Capacitance			2	pF	$I_E = 0, V_{CB} = 5V$
C <sub>C1C2</sub>	Collector to Collector Capacitance			4	pF	V <sub>CC</sub> = 0V
I <sub>C1C2</sub>	Collector to Collector Leakage Current			10	nA	$V_{CC} = \pm 60V$
$f_{T}$	Current Gain Bandwidth Product	110			MHz	$I_{C} = 1 \text{mA}, V_{CE} = 5 \text{V}$
NF	Narrow Band Noise Figure			3	dB	$I_C = 100 \mu A$ , $V_{CE} = 5V$ , $BW = 200 Hz$ , $R_G = 10 K\Omega$ ,
						f = 1KHz

#### Notes:

- 1. Absolute Maximum ratings are limiting values above which serviceability may be impaired
- 2. The reverse base-to-emitter voltage must never exceed 6.2 volts; the reverse base-to-emitter current must never exceed 10µA.

Available Packages:

LS130A in TO-71 LS130A available as bare die



Please contact Micross for full package and die dimensions:

Email: <a href="mailto:chipcomponents@micross.com">chipcomponents@micross.com</a>
Web: <a href="mailto:www.micross.com/distribution.aspx">www.micross.com/distribution.aspx</a>

TO-71 (Bottom View)

